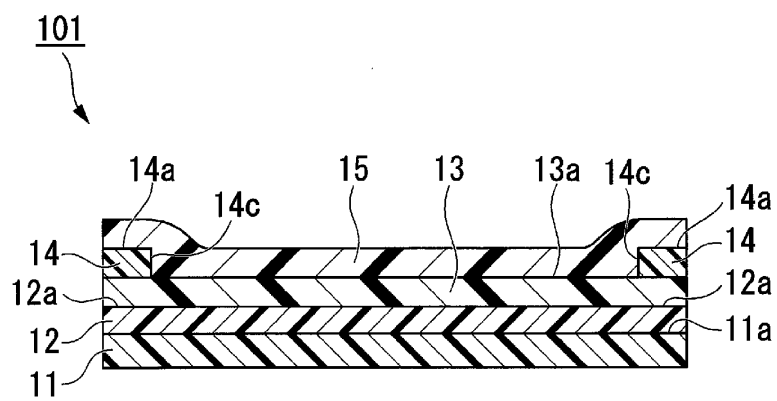
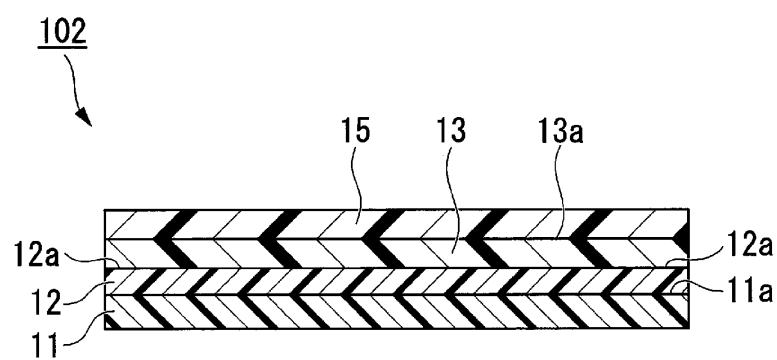


[図1]



[図2]

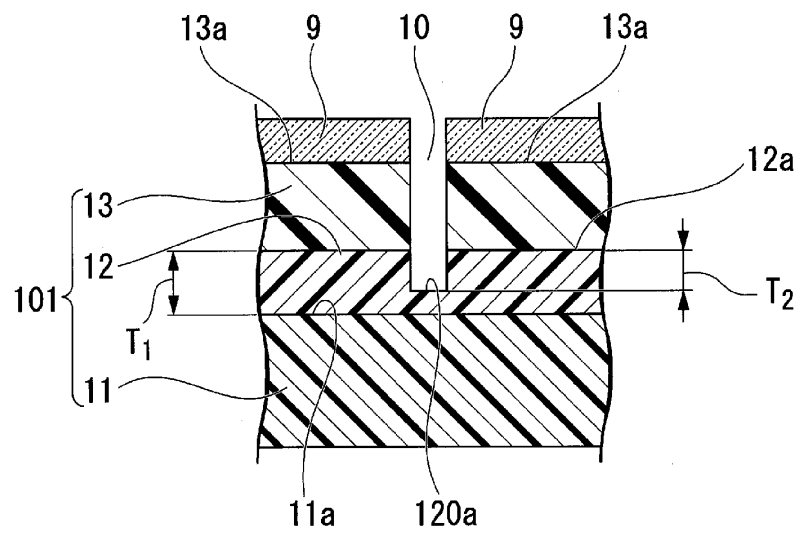


A cross-sectional view of a semiconductor device 103. The device consists of a substrate 103 with a base layer 11. A layer 12 is formed on the base layer 11. A layer 15 is formed on the layer 12. A layer 23 is formed on the layer 15. A layer 23a is formed on the layer 23. A layer 23c is formed on the layer 23a. A layer 12a is formed on the layer 23c. A layer 11a is formed on the layer 12a.

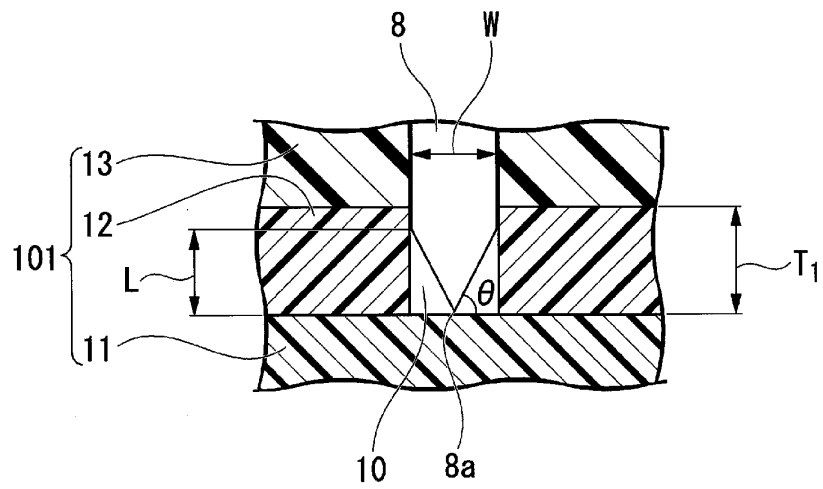
(a) Cross-sectional view of the semiconductor device before etching. The device consists of a substrate 101 with layers 11, 12, and 13. A gate stack 9' is formed on the substrate, and a gate stack 9a' is formed on the gate stack 9'. A gate stack 13a is formed on the gate stack 9a'. A gate stack 14 is formed on the gate stack 13a. A gate stack 201 is formed on the gate stack 14.

(b) Cross-sectional view of the semiconductor device after etching. The gate stack 9' has been etched away, leaving the gate stack 9a' and the gate stack 13a. The gate stack 14 and the gate stack 201 remain on the gate stack 13a. The gate stack 10 is formed on the gate stack 9a'.

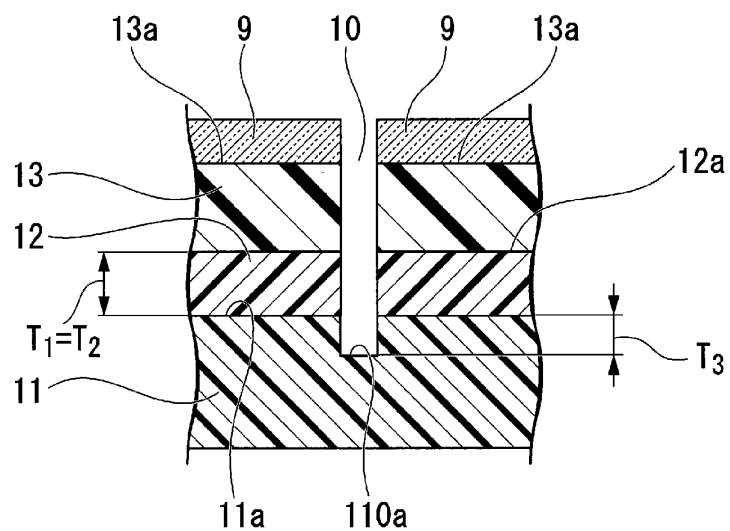
[図5]



[図6]



[図7]



[図8]

